

In the Claims:

1.-7. (Canceled)

8. (Previously Presented) The method according to Claim 50, wherein the conductive lines comprise copper.

9.-49. (Canceled)

50. (Currently Amended) A method of fabricating a semiconductor device, the method comprising:

disposing a workpiece in a processing chamber;

disposing a first dielectric material over the workpiece, while said workpiece is in said processing chamber;

disposing a second dielectric material over the first dielectric material, the second dielectric material comprising a different material than the first dielectric material, wherein the first dielectric material and the second dielectric material comprise a first insulating layer;

depositing a hard mask over the second dielectric material, the depositing of said hard mask comprising depositing a first mask layer, depositing a second mask layer over said first mask layer and depositing a third mask layer over the second mask layer;

forming a first pattern in the first dielectric material;

cleaning the processing chamber while the workpiece remains in the processing chamber, and before removing without etching any of the layers of the material on the workpiece;

forming a second pattern different from the first pattern in the second dielectric material wherein forming said patterns comprises;

patterning at least the third mask layer with the second pattern;  
patterning the third mask layer, the second mask layer and the first mask layer  
with the first pattern;  
transferring the first pattern to the second dielectric material;  
removing the third mask layer, the second mask layer and the first mask layer in  
the second pattern regions;  
transferring the first pattern to the first dielectric material; and  
removing the second dielectric material in the second pattern regions, subsequent to said  
step of cleaning.

51. (Previously Presented) The method according to Claim 50, wherein the second dielectric material comprises a top surface, further comprising:

depositing a conductive material over the patterned second dielectric material and the  
patterned first dielectric material; and  
removing the conductive material from the top surface of the second dielectric material.

52. (Previously Presented) The method according to Claim 51, wherein removing the  
conductive material from the top surface of the second dielectric material comprises forming  
conductive lines in the second pattern of the second dielectric material.

53. (Previously Presented) The method according to Claim 51, wherein the conductive  
material forms vias in the first pattern of the first dielectric material.

54. (Previously Presented) The method according to Claim 53, wherein the vias comprise substantially vertical sidewalls.

55. (Previously Presented) The method according to Claim 53, wherein the workpiece comprises component regions, wherein at least one of the vias makes electrical contact with a component region of the workpiece.

56. (Previously Presented) The method according to Claim 54, wherein the workpiece component regions comprise a plurality of conductive lines formed in a dielectric layer.

57. (Previously Presented) The method according to Claim 56, wherein the conductive lines comprise copper, wherein disposing the first dielectric material comprises disposing a material having a coefficient of thermal expansion (CTE) close to the CTE of the conductive lines.

58. (Previously Presented) The method according to Claim 50, wherein depositing the first mask layer comprises depositing  $\text{SiC}_x$ ,  $\text{SiC}_x\text{N}_y$ ,  $\text{SiC}_x\text{H}_y$ ,  $\text{SiC}_x\text{N}_y\text{H}_z$ , or  $\text{SiCOH}$ , wherein depositing the second mask layer comprises depositing  $\text{Si}_x\text{N}_y$  or  $\text{SiO}_2$ , and wherein depositing the third mask layer comprises depositing a refractory metal nitride.

59. (Previously Presented) The method according to Claim 58, wherein depositing the first mask layer comprises depositing a layer of  $\text{SiC}_x$  and a layer of  $\text{N-SiC}_x$  over the layer of  $\text{SiC}_x$ .

60. (Previously Presented) The method according to Claim 50, wherein cleaning the processing chamber comprises introducing a plasma cleaning gas comprising  $\text{O}_2$  gas diluted in

Ar, He, or N<sub>2</sub>, and wherein the plasma cleaning gas removes polymer build-up on the processing chamber walls.

61. (Previously Presented) The method according to Claim 60, further comprising only applying power to an electrode in the chamber during cleaning, wherein the workpiece is not biased during the cleaning method, and wherein the plasma electrode power density applied comprises about 0.1 W/cm<sup>2</sup> to 10 W/cm<sup>2</sup> at a pressure of about 50 mTorr to 500 mTorr.

62. (Previously Presented) The method according to Claim 50, further comprising:  
depositing a cap layer over the workpiece, before disposing the first dielectric material;  
and  
transferring the first pattern to the cap layer.

63. (Previously Presented) The method according to Claim 62, further comprising forming an adhesion film over a top surface of the cap layer.

64. (Previously Presented) The method according to Claim 50, further comprising forming an adhesion film disposed over a top surface of the first dielectric layer.

65. (Previously Presented) The method according to Claim 50, wherein forming the first pattern and the second pattern further comprises:  
after patterning at least the third mask layer with the second pattern, depositing an anti-reflective coating over the third mask layer;  
depositing a photoresist layer over the anti-reflective coating;

patterning the photoresist layer with the first pattern; and  
transferring the first pattern in the photoresist layer to the third mask layer, the second mask layer, the first mask layer, and the second dielectric layer.

66. (Previously Presented) The method according to Claim 50, wherein disposing the first dielectric material comprises disposing an inorganic material, and wherein disposing the second dielectric material comprises disposing an organic material.

67. (Previously Presented) The method according to Claim 50, wherein disposing the first dielectric material comprises disposing a material that is etchable selective to the second dielectric material.

68. (Previously Presented) The method according to Claim 50, wherein disposing the first dielectric material comprises disposing undoped silicate glass (USG), fluorinated silicon glass (FSG), fluorinated tetraethoxysilane (FTEOS), SiCOH, or porous-SiCOH, and wherein disposing the second dielectric material comprises disposing SiLK<sup>TM</sup> or porous-SiLK<sup>TM</sup>.

69. (Previously Presented) A method of fabricating a semiconductor device, the method comprising:

disposing a workpiece in a processing chamber;

disposing a first dielectric material over the workpiece;

disposing a second dielectric material over the first dielectric material, the second dielectric material comprising a different material than the first dielectric material, and wherein the first dielectric material and the second dielectric material comprise a first insulating layer;

depositing a hard mask over the second dielectric material, the deposition of said hard mask comprising depositing a first mask layer, depositing a second mask layer over said first mask layer and depositing a third mask layer over the second mask layer;

forming a first pattern in the first dielectric material;

moving the workpiece to another processing chamber and then removing the second dielectric material to form a second pattern, said second pattern different from the first pattern; and

said steps of forming said first and second patterns comprising;

patterning at least the third mask layer with the second pattern;

patterning the third mask layer, the second mask layer and the first mask layer with the first pattern;

transferring the first pattern to the second dielectric material;

removing the third mask layer, the second mask layer and the first mask layer in the second pattern regions;

transferring the first pattern to the first dielectric material; and

removing the second dielectric material in the second pattern regions.

70. (Previously Presented) The method of Claim 64, wherein the second dielectric material comprises a top surface, further comprising:

depositing a conductive material over the patterned second dielectric material and the patterned first dielectric material; and

removing the conductive material from the top surface of the second dielectric material.

71. (Previously Presented) The method of Claim 65, wherein removing the conductive material from the top surface of the second dielectric material to form comprises forming conductive lines in the second pattern of the second dielectric material.

72. (Previously Presented) The method of Claim 66, wherein the conductive lines comprise copper, wherein disposing the first dielectric material comprises disposing a material having a coefficient of thermal expansion (CTE) close to the CTE of the conductive lines.